



On a Shockley-Read-Hall Model for Semiconductors: Convergence to Equilibrium

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We are considering a drift-diffusion and a kinetic model for the flow of electrons in a semiconductor crystal, incorporating the effects of recombination-generation via traps distributed in the forbidden band. In mathematical terms, model consists of a reaction-diffusion-convection equation for the electric field and an integro-differential equation for the distribution of occupied traps. We derive formal and rigorous asymptotics, and show convergence.



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